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Patent Number: JP1009895
Publication date: 1989-01-13
Inventor(s): MATSUMOTO TAKU
Applicant(s): NEC CORP
Requested Patent: ☐ JP1009895
Application Number: JP19870165694 19870701
Priority Number(s):
IPC Classification: C30B29/40; C30B25/14
EC Classification:
EC Classification:
Equivalents:

Abstract

PURPOSE: To form the titled superconductor crystal, having good crystallinity and capable of selective growth on a substrate, by alternately feeding a gas species containing In chloride and a gas species containing a group V constituent element onto a silicon substrate having a formed mask pattern.

CONSTITUTION: An In source boat 12 is placed on the upstream side of a growth chamber 11 in the lower stage and a carrier gas and HCl gas are fed from the upstream side thereof to adsorb the formed In chloride on a silicon substrate 14 having a formed mask pattern. The substrate 14 is then moved to a growth chamber 13 in the upper stage and a gas species containing a group V constituent element is fed and adsorbed on the substrate 14. The above-mentioned operations are alternately repeated to carry out atomic layer epitaxial growth of a III-V compound semiconductor crystal on the substrate 14.